

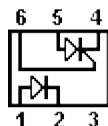
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H11C4-H11C6 OPTICALLY COUPLED SCR ISOLATOR

Circuit



Features

- Photo-SCR Output
- 1060-1500 V Isolation
- 400 V_{peak} Forward Voltage
- Low Cost Dual-In-Line Package

Description

The H11C4-H11C6 are optically-coupled isolators consisting of a Gallium Arsenide infrared emitting diode and light activated silicon controlled rectifier (SCR) mounted in a standard 6-pin dual-in-line package. Surface Mount Option Available.
All electrical parameters are 100% tested. Specifications are guaranteed to a cumulative 0.65% AQL.

Absolute Maximum Ratings: (Ta=25°C)

| | |
|--|---|
| Storage Temperature: | -55°C to +150°C |
| Operating Temperature: | -55°C to +100°C |
| Lead Soldering: | 260°C for 10s, 1.6mm from case |
| Input-to-Output Isolation Voltage, Steady State: | ±1060 Vdc (H11C5-C6) ±1500 Vdc (H11C4) |

Input Diode

| | |
|------------------------|----------------------|
| Forward DC Current: | 60mA |
| Reverse DC Voltage: | 5V |
| Peak Forward Current): | 3A (1µs p.w. 300pps) |
| Power Dissipation: | 100mW |
| Derate Linearly: | 1.33mW/°C above 25°C |

Output Photo SCR

| | |
|-------------------------|---------------------------|
| Peak Forward Voltage: | 400V |
| RMS Forward Current: | 300mA |
| Forward Current (Peak): | 10A (100µs 1% duty cycle) |
| Surge Current: | 5A (10ms) |
| Reverse Gate Voltage: | 6V |

Package

| | |
|--------------------|---------------------|
| Power Dissipation: | 400mW |
| Derate Linearly: | 5.3mW/°C above 25°C |

Electro-optical Characteristics: (Ta=25°C)

| INPUT | PARAMETER | CONDITIONS | VALUE | |
|-----------------|----------------------------|--|--------|-----|
| V _F | Forward Voltage | I _F =10mA | 1.5 V | Max |
| I _R | Reverse Current | V _R =3.0V | 10 µA | Max |
| V _R | Reverse Breakdown Voltage | I _R =10µA | 6.0 V | Min |
| OUTPUT | PARAMETER | CONDITIONS | VALUE | |
| V _{DM} | Peak Off-State Voltage | R _{GK} =10kohm, T _A =100°C | 400 V | Min |
| V _{RM} | Peak Reverse Voltage | | 400 V | Min |
| V _{TM} | On-State Voltage | I _{TM} =0.3mA | 1.3 V | Max |
| I _{DM} | Off-State Current | V _{DM} =400V, T _A =100°C | 150 µA | Max |
| I _{RM} | Reverse Current | V _{RM} =400V, T _A =100°C | 150 µA | Max |
| | Capacitance (Anode-Gate) | V=0,f=1MHz | 24 pF | Typ |
| | Capacitance (Gate-Cathode) | | 360 pF | Typ |
| COUPLED | PARAMETER | CONDITIONS | VALUE | |
| | Input Current to Trigger | | | |

| | | | | |
|-----------------|-----------------------------------|--|-----------|-----|
| I _{FT} | H11C4, H11C5 | V _{AK} =50V, R _{GK} =10kohm | 20 mA | Max |
| | H11C6 | | 30 mA | Max |
| | H11C4, H11C5 | V _{AK} =100V, R _{GK} =27kohm | 11 mA | Max |
| | H11C6 | | 14 mA | Max |
| R _{IO} | Isolation Resistance | V _{IO} =500V, (note 1) | 100 Gohm | Min |
| | Input to Output Capacitance | V _{IO} =0, f=1MHz | 2 pF | Max |
| | dV/dt Input to Output | Figure 1 | 500 V/μs | Min |
| | Input-to-Output Isolation Voltage | | | |
| | H11C4 | (Note 1) | 1500 Vrms | Min |
| | H11C5,H11C6 | | 1060 Vrms | Min |

Notes

1. Measured with input leads shorted together and output leads shorted together.

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